
2SB1530

Silicon PNP Triple Diffused

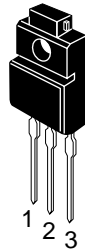
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Application

Low frequency power amplifier color TV vertical deflection output complementary pair with 2SD2337

Outline

TO-220FM



1. Base
2. Collector
3. Emitter

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-200	V
Collector to emitter voltage	V_{CEO}	-150	V
Emitter to base voltage	V_{EBO}	-6	V
Collector current	I_{C}	-2	A
Collector peak current	$I_{\text{C(peak)}}$	-5	A
Collector power dissipation	P_{C}	1.5	W
	P_{C}^{*1}	20	
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-45 to +150	$^\circ\text{C}$

Note: 1. Value at $T_{\text{C}} = 25^\circ\text{C}$.

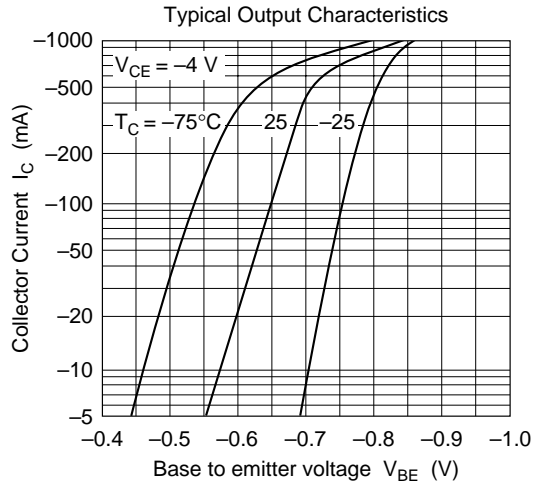
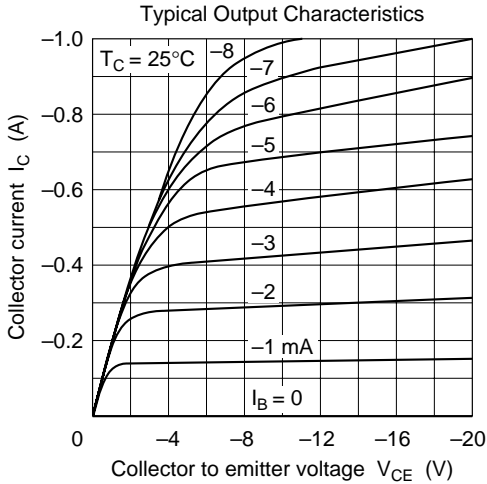
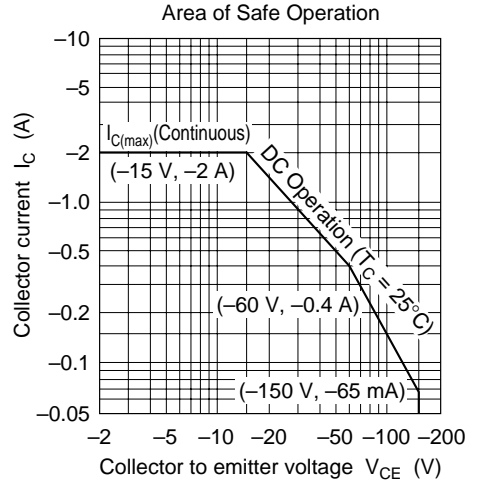
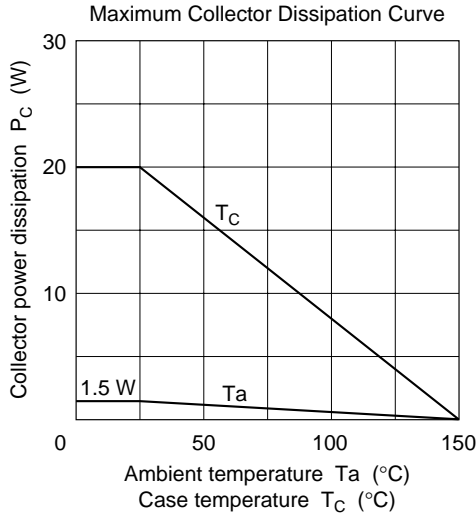
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

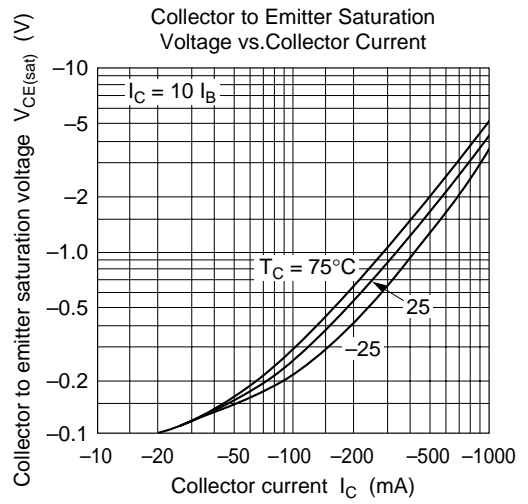
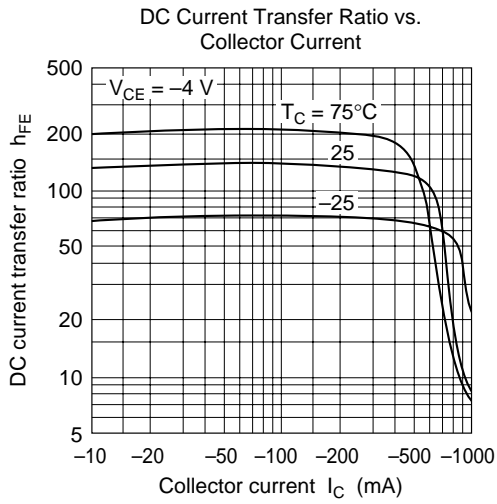
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	-150	—	—	V	$I_{\text{C}} = -50 \text{ mA}$, $R_{\text{BE}} = \infty$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	-6	—	—	V	$I_{\text{E}} = -5 \text{ mA}$, $I_{\text{C}} = 0$
Collector cutoff current	I_{CBO}	—	—	-1	μA	$V_{\text{CB}} = -120 \text{ V}$, $I_{\text{E}} = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{\text{CE}} = -4 \text{ V}$, $I_{\text{C}} = -50 \text{ mA}$
	h_{FE2}	60	—	—		$V_{\text{CE}} = -10 \text{ V}$, $I_{\text{C}} = -500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	-3	V	$I_{\text{C}} = -500 \text{ mA}$, $I_{\text{B}} = -50 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-1	V	$I_{\text{CE}} = -4 \text{ A}$, $I_{\text{C}} = -50 \text{ mA}$

Notes: 1. The 2SB1530 is grouped by h_{FE1} as follows.

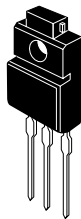
B	C
60 to 120	100 to 200

2. Pulse test.





Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.8 g

Cautions

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